

ABSTRACT OF THE INVENTION

There is provided a mask blank, including: a thin film 11 for forming a transfer pattern; a resist underlying film 12 made of a resist underlying composition and provided on the thin film; a resist film 13 made of a chemically amplified resist and provided on the resist underlying film 12; and a mixture film 14 provided so as to be interposed between the resist underlying film 12 and the resist film 13, wherein the resist underlying film 12 is configured so that a molecular weight is reduced from the thin film 11 side to the resist film 13 side in a thickness direction, and has a low molecular weight region 12a in which the molecular weight is low on the resist film 13 side surface, and the mixture film 14 is formed by mixing a component of the low molecular weight region 12a and a component of the chemically amplified resist.